Electronic Supplementary Information

Solar Hydrogen Production over Novel Metal Sulfide Photocatalysts of AGa₂In₃S₈ (A=Cu or Ag) with Layered Structures

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Fig. S1 Crystal structure of $Ag_{1.12}Ga_{2.68}In_{3.7}S_{10}$.¹³



Fig. S2 X-ray diffraction patterns of (a) $Ag_{1.12}Ga_{2.68}In_{3.7}S_{10}$ (PDF 01-070-8366), (b) $CuGa_2In_3S_8$ prepared at 1023 K, (c) $CuGa_2In_3S_8$ prepared at 1123K, (d) $CuGa_2In_3S_8$ prepared at 1273 K, (e) $AgGa_2In_3S_8$ prepared at 1223 K and (f) $AgGa_2In_3S_8$ prepared with 40%-excess Ga_2S_3 at 1223 K. Samples (b)-(e) were prepared without excess Ga_2S_3 .



Fig. S3 Scanning electron microscope images and surface areas of (a), (b) $CuGa_2In_3S_8$ prepared at 1273 K, (c) $CuGa_2In_3S_8$ prepared at 1123K and (d) $AgGa_2In_3S_8$ prepared at 1223 K with 40%-excess Ga_2S_3 . Samples (a)-(c) were prepared without excess Ga_2S_3 .



Fig. S4 Diffuse reflectance spectra of (a) $AgGa_2In_3S_8$ prepared at 1223 K without excess Ga_2S_3 , (b) $AgGa_2In_3S_8$ prepared at 1223 K with 40%-excess Ga_2S_3 and (c) $AgIn_5S_8$ prepared at 1273 K.